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TI Silicon carbide-metal joint
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SO Jpn. Kokai Tokkyo Koho, 3 pp.
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AB	SiC and Cu or Cu alloy is joined by an interlayer of .gtoreq.2 layers, of Ti, Ag, and/or Cu to form substrates for semiconductor circuits. The interlayer may contain a Ni or Ni-based inside layer. A sintered SiC plate was polished on a side and washed with Me2CO for joining. A Cu plate was washed with dil. HNO3. A layer Ag-28% Cu alloy, a layer of Ti, and a layer of Ag-28% Cu were laid. successively on the polished ceramic surface, the Cu plate was placed on top, and the stack was heated at 1000.degree. and <100 g/cm2 in a 10-4 torr vacuum for 5 min. The obtained laminate had the Cu plate in compact joint with the SiC plate.				